

YJ Planar Schottky Barrier Diode Die Specification

150V 1A, 32mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB032H150SS-280A

Main Products Characterstics

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 1\text{ A}$

$\leq 2\%$

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Note: 1 * : Also can offer device with 8 mils thickness
- 2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

does not guarantee device performance after assembly.

Store in original container, in dessicated nitrogen, with no contamination.

Operating pa MCIDMCID 25Ang (x-none)BDC 0916 71f1tID 25reWhBTf3 6.72 Tf1 0 0 1 0 1m3 6.7 0 0 bce th noblyno